

**POWER MOS V® FREDFET**

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



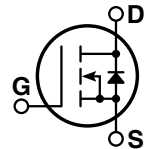
- **Faster Switching**

- **Avalanche Energy Rated**

- **Lower Leakage**

- **FAST RECOVERY BODY DIODE**

- **Popular SOT-227 Package**


**MAXIMUM RATINGS**

 All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT40M35JVFR	UNIT
$V_{DSS}$	Drain-Source Voltage	400	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	93	Amps
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	372	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	700	Watts
	Linear Derating Factor	5.6	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive)	93	Amps
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy <sup>④</sup>	3600	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ )	400			Volts
$I_{D(on)}$	On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10\text{V}$ )	93			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10\text{V}, I_D = 46.5\text{A}$ )			0.035	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = 400\text{V}, V_{GS} = 0\text{V}$ )			250	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 320\text{V}, V_{GS} = 0\text{V}, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 5\text{mA}$ )	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

**DYNAMIC CHARACTERISTICS**

**APT40M35JVFR**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V		16800	20160	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25V		2400	3360	
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		1070	1605	
Q <sub>g</sub>	Total Gate Charge ③	V <sub>GS</sub> = 10V		710	1065	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DD</sub> = 200V		80	120	
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	I <sub>D</sub> = 93A @ 25°C		340	510	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = 15V		20	40	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 200V		30	60	
t <sub>d(off)</sub>	Turn-off Delay Time	I <sub>D</sub> = 93A @ 25°C		75	115	
t <sub>f</sub>	Fall Time	R <sub>G</sub> = 0.6Ω		14	28	

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I <sub>S</sub>	Continuous Source Current (Body Diode)			93	Amps
I <sub>SM</sub>	Pulsed Source Current ① (Body Diode)			372	
V <sub>SD</sub>	Diode Forward Voltage ② (V <sub>GS</sub> = 0V, I <sub>S</sub> = - 93A)			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑤			15	V/ns
t <sub>rr</sub>	Reverse Recovery Time (I <sub>S</sub> = -93A, di/dt = 100A/μs)	T <sub>J</sub> = 25°C		300	ns
		T <sub>J</sub> = 125°C		600	
Q <sub>rr</sub>	Reverse Recovery Charge (I <sub>S</sub> = -93A, di/dt = 100A/μs)	T <sub>J</sub> = 25°C		2.2	μC
		T <sub>J</sub> = 125°C		9	
I <sub>RRM</sub>	Peak Recovery Current (I <sub>S</sub> = -93A, di/dt = 100A/μs)	T <sub>J</sub> = 25°C		16	Amps
		T <sub>J</sub> = 125°C		33	

**THERMAL/PACKAGE CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Junction to Case			0.18	°C/W
R <sub>θJA</sub>	Junction to Ambient			40	
V <sub>Isolation</sub>	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations			10	lb•in

① Repetitive Rating: Pulse width limited by maximum junction temperature.

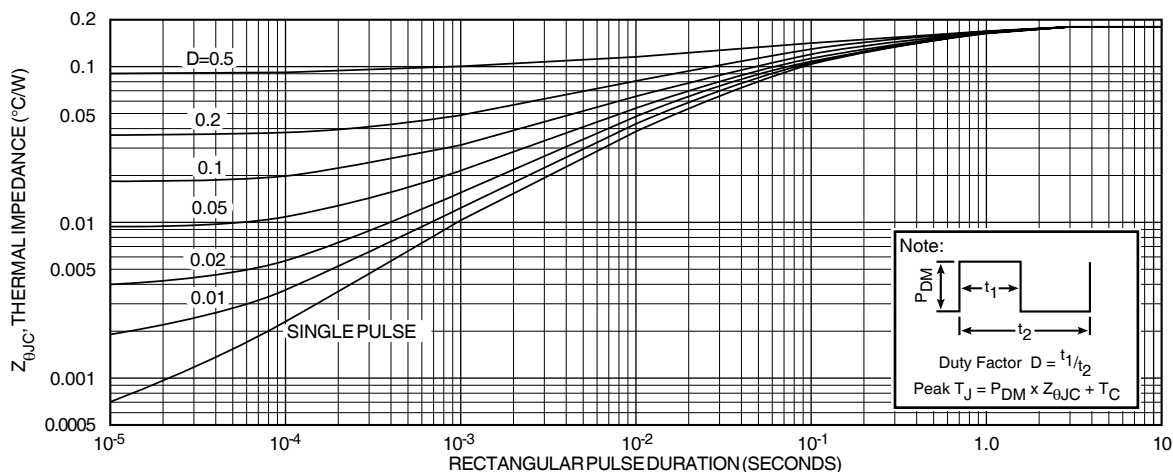
② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T<sub>J</sub> = +25°C, L = 0.83mH, R<sub>G</sub> = 25Ω, Peak I<sub>L</sub> = 93A

⑤ I<sub>S</sub> ≤ I<sub>D</sub> = 93A, di/dt = 100A/μs, T<sub>J</sub> ≤ 150°C, R<sub>G</sub> = 2.0Ω V<sub>R</sub> = 400V.

**APT Reserves the right to change, without notice, the specifications and information contained herein.**



**FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION**

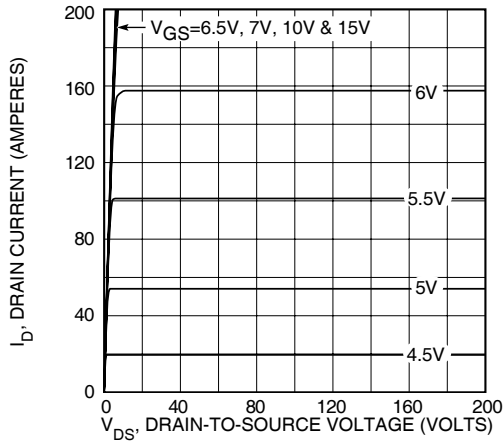


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

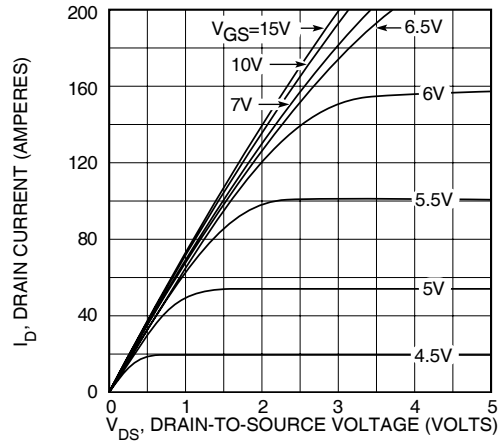


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

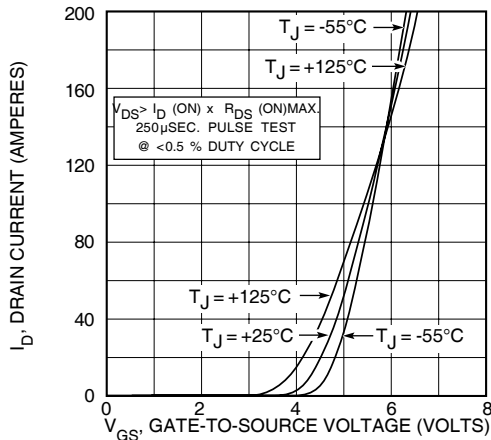


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

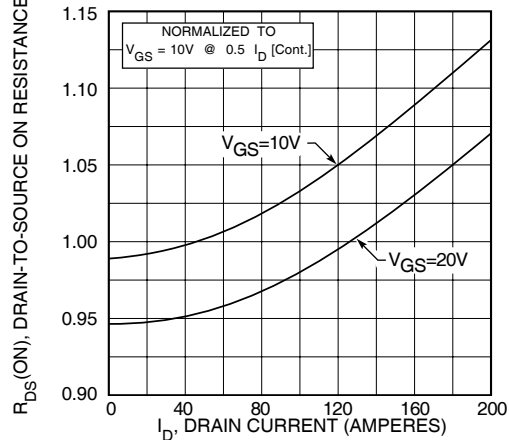


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

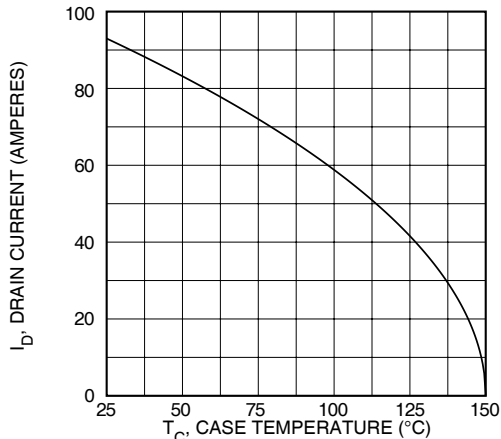


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

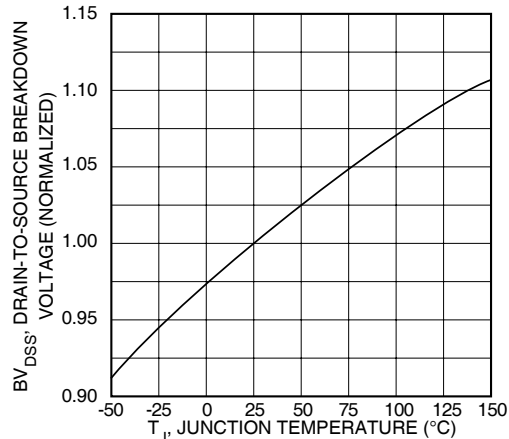


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

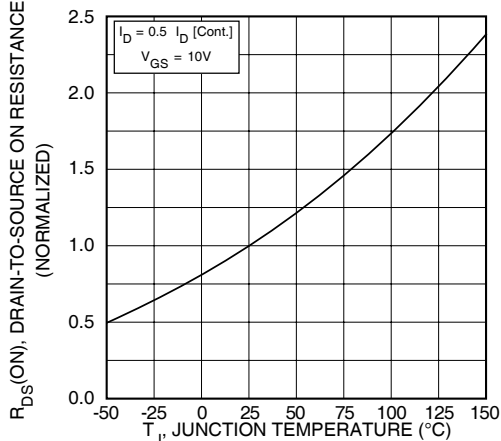


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

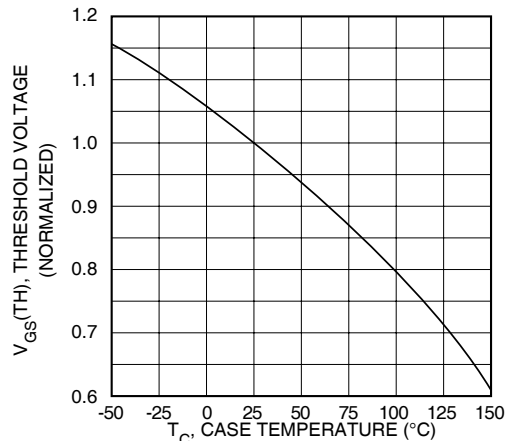


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

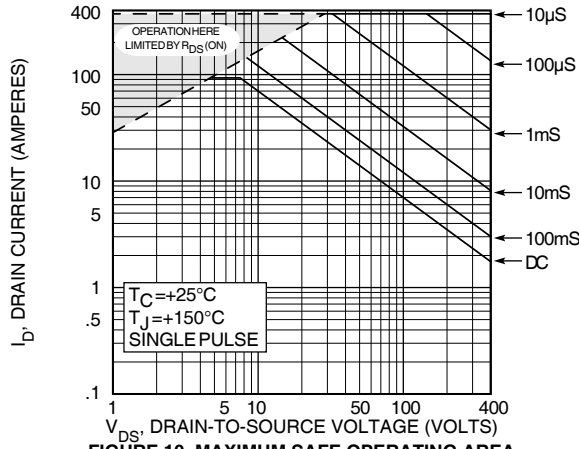


FIGURE 10, MAXIMUM SAFE OPERATING AREA

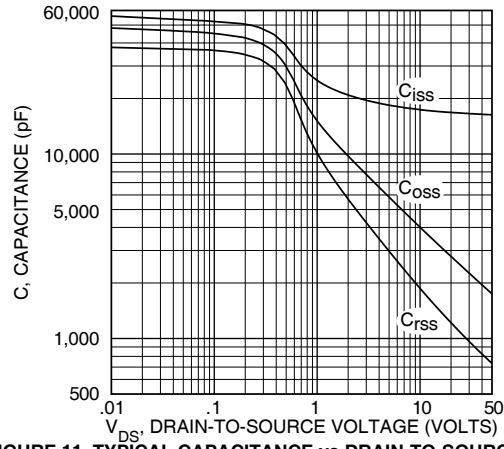


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

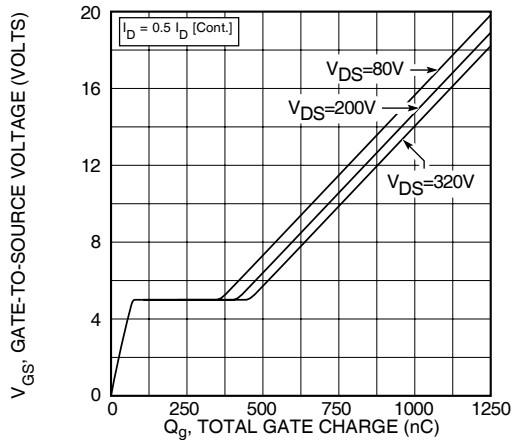


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

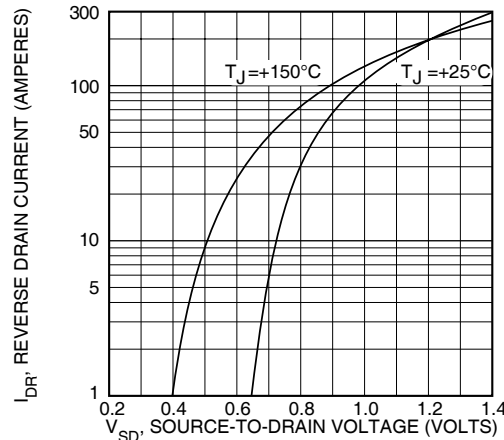
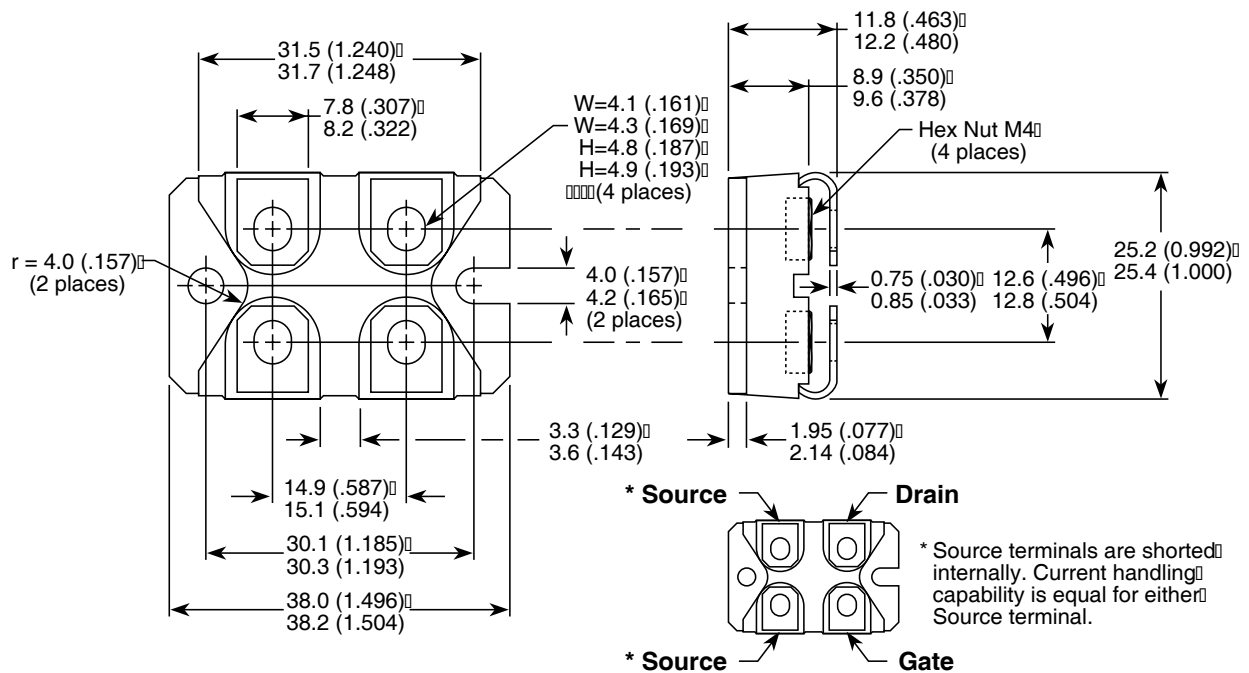


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)